AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently Amended) An etching method for etching an etching target film formed on an SiO_2 film placed inside an airtight processing chamber, the method comprising:

introducing a processing gas into said airtight processing chamber, wherein said processing gas contains N_2 and at least one of C_4F_8 and CF_4; ~~and~~

generating a plasma in said airtight processing chamber for etching said etching target film, and

etching an organic target film containing Si formed on the SiO_2 film until the SiO_2 film is exposed ~~wherein said etching target film is an organic film containing Si formed on said SiO_2 film~~, wherein a resist is used as a mask on said etching target film~~, and wherein said etching target film is etched until said SiO_2 film is exposed~~.

2. (Currently Amended) An etching method according to claim 1, wherein[[:]] said organic film containing Si is constituted of SiO_2 containing C and H.

3. (Currently Amended) An etching method according to claim 1, wherein[[:]] the dielectric constant of said organic film containing Si is equal to or lower than 3.0.

4. (Currently Amended) An etching method according to claim 1, wherein[[:]] said organic target film containing Si is an organic polysiloxane film.

5. (Currently Amended) An etching method according to claim 1, wherein[[:]] said processing gas further contains Ar.

Claims 6-13 (Canceled).

14. (Currently Amended) An etching method for etching an etching target film formed on an SiO_2 film placed inside an airtight processing chamber, the method comprising:

introducing a processing gas into said airtight processing chamber, wherein said processing gas contains at least CF_4 and N_2, wherein the flow rate ratio of CF_4 and N_2 in said processing gas is essentially set within a range of $1 \leq (N_2$ flow rate / CF_4 flow rate) ≤ 4; ~~and~~

generating a plasma in said airtight processing chamber for etching said etching target film, and

etching an organic target film containing Si formed on the SiO_2 film until the SiO_2 film is exposed ~~wherein said etching target film is an organic film containing Si formed on said SiO_2 film~~, wherein a resist is used as a mask on said etching target film~~, and wherein said etching target film is etched until said SiO_2 film is exposed~~.

Claims 15 -17 (Canceled).